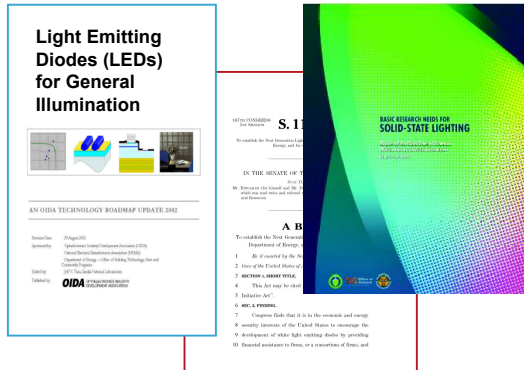
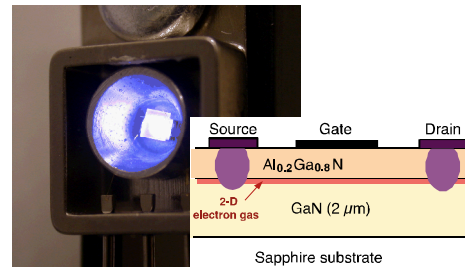


Ultra Wide-Bandgap Grand Challenge at Sandia

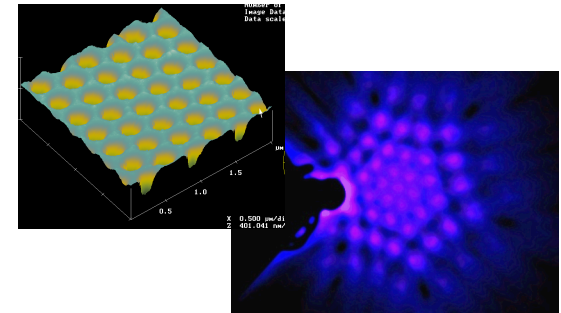
1999-2006: Comprehensive US Technology Roadmaps



2003-2007: high power amplifiers, UV emitters



2000-2004: SSL Grand Challenge LDRD



2009-2014: DOE EFRC for SSL Science



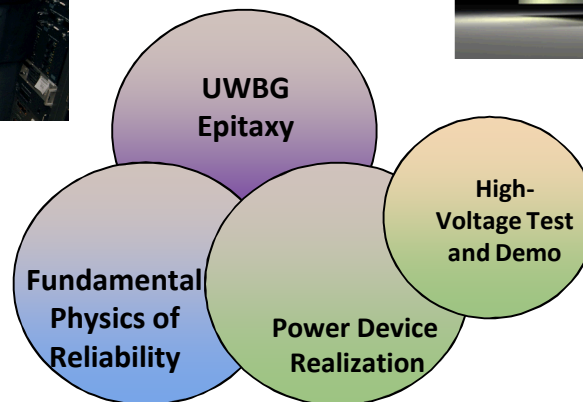
2006-2008: DOE /EERE National Center for SSL



2003-2012: DOE-Funded Collaborations with industry



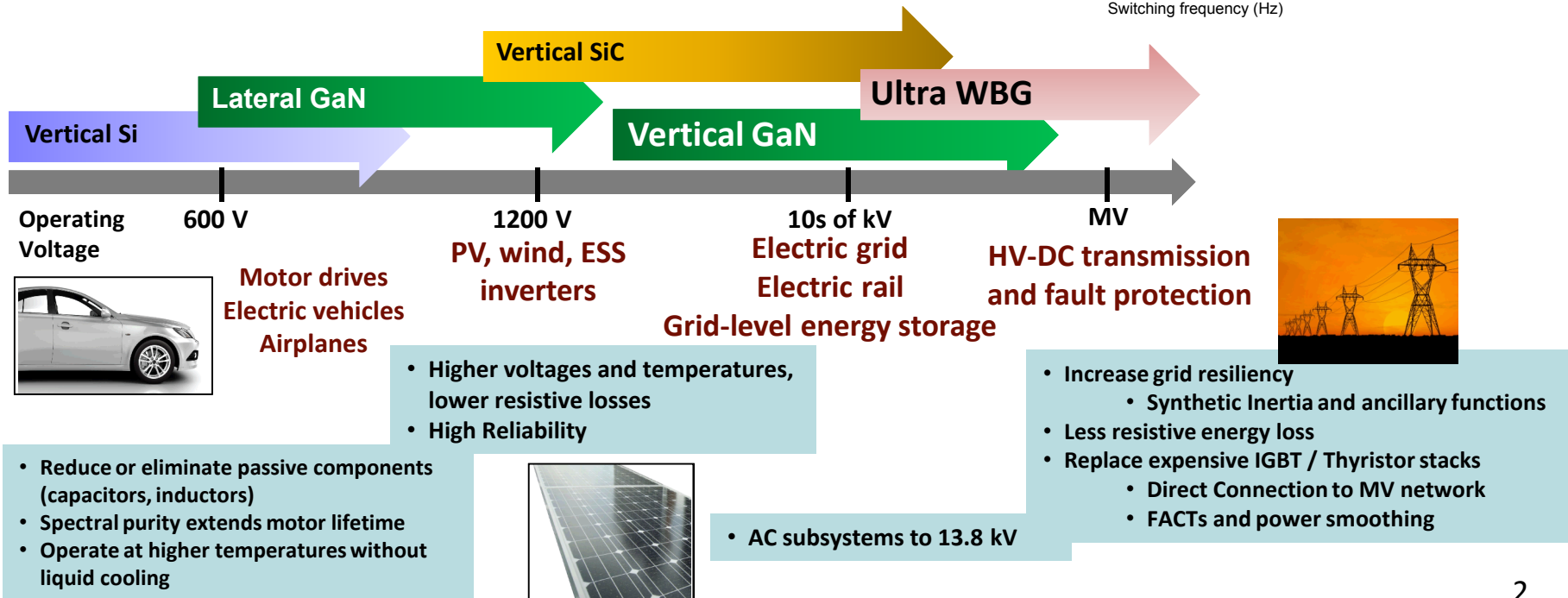
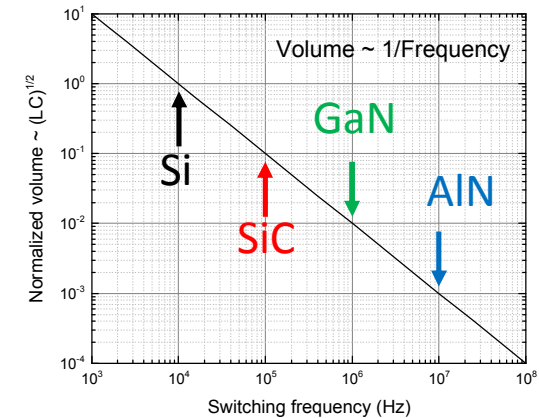
GeneSiC SiC Thyristors



- 60+ years as DOE/NNSA mission lead in electronics
- 30+ years of compound semiconductor research
- 20+ years of wide band gap materials & device R&D

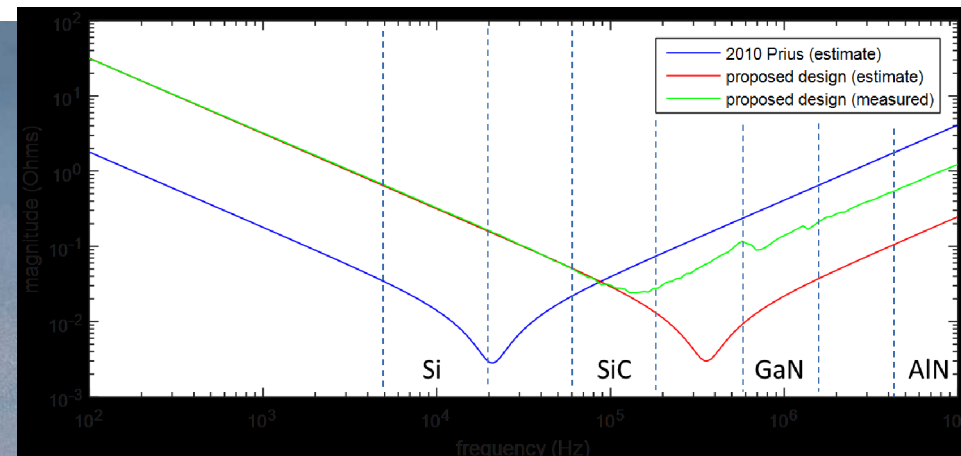
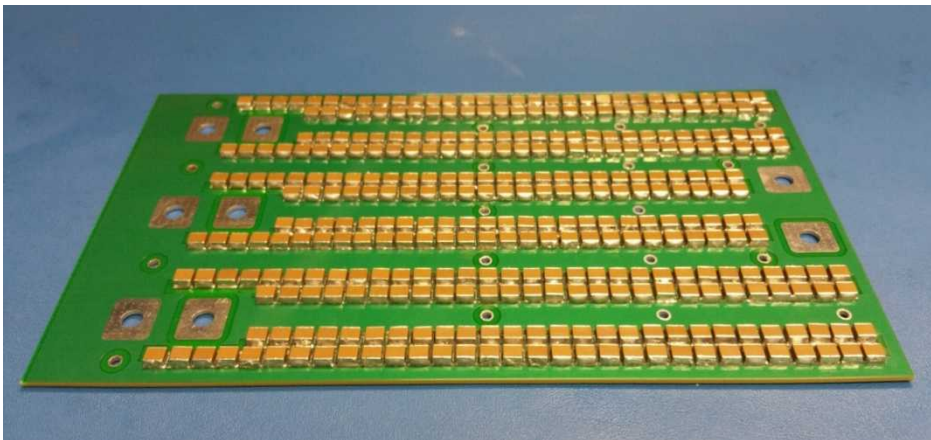
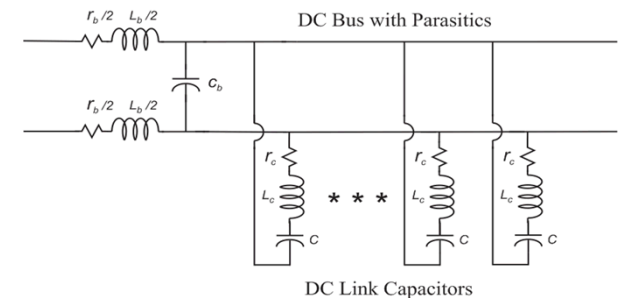
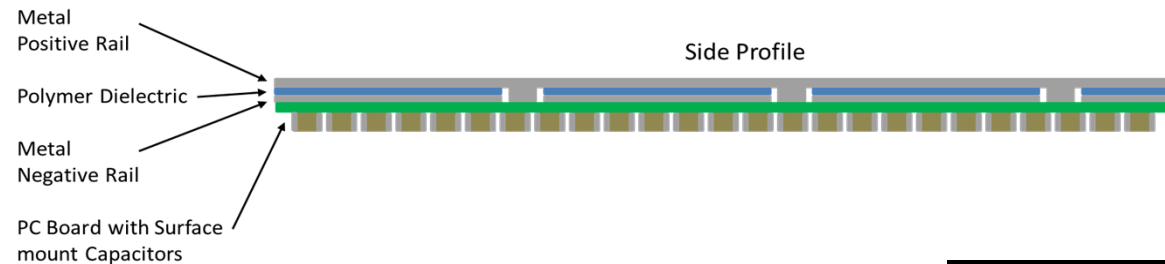
Wide Bandgap SWaP

- Current power electronics are limited by the properties of Silicon devices
- New system capabilities are enabled by:
 - Higher switching frequency (enables better SWaP)
 - Lower power loss
 - Higher temperature operation
 - Greater breakdown voltage



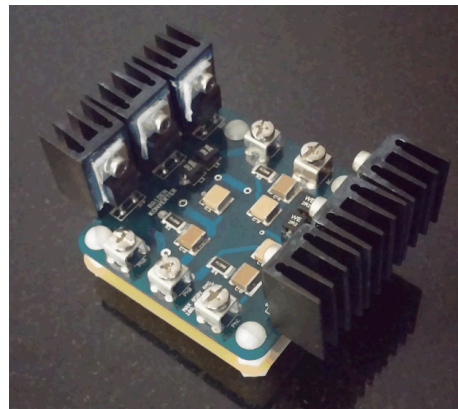
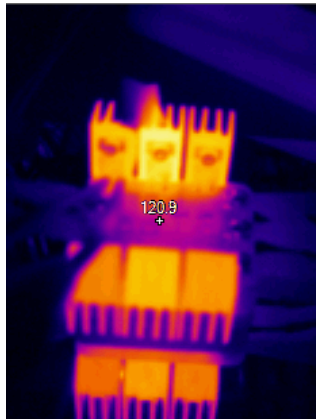
Wide Bandgap SWaP

- High-Power inverter applications (i.e. PV inverters, electric vehicles, ...) have a DC link with substantial smoothing capacitance
 - Conventional film capacitors → large ESL, low resonances (~10kHz), reliability issue
- PCB approach to replace bulky capacitors with SMB ceramic capacitors
 - low-ESL → high resonance suitable for WBG devices
 - low-ESR → low loss
 - easy manufacturability → low cost and high reliability



Wide Bandgap SWaP

- A 6-pulse rectifier built and tested
 - 3-Phase AC in, DC out
 - Passive → no controller
- 6 Avogy GaN diodes and EMI filter on a PCB
- Devices rated for 1200 V / 5 A
 - Practical for 800V_{AC} RMS / 900V_{DC}
- Converter tested using 10 kVA, 400 Hz PM generator
- Converter tested to:
 - 43 W/in³ at 300 V → 150 W/in³ (theoretical) at full voltage
 - 4.25 kW/kg
 - 130°C junction temperature (est)



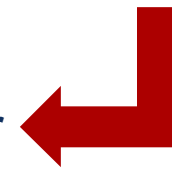
MacBook Air (45W)



20.6 W/in³



Current SOA with GaN WBG
Avogy Zolt (70W)



Sandia rectifier
550 W, 12.8 in³
43 W/in³ (demonstrated)